IN THE CLAIMS

Please cancel claims 1-22 after adding new claims 23-43 as follows:

23. [New] A semiconductor device comprising:

an oxide active area;

at least one feature over the oxide active area, the feature having a surface and being contiguous with the oxide active area at a boundary; and

a spacer covering the surface of the feature and terminating at the boundary wherein the spacer is not in contact with the oxide active area.

24. [New] The semiconductor device of claim 23 wherein:

the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;

the spacer comprises silicon nitride or an amorphous silicon film; and

the surface of the feature comprises sidewalls of the electrode.

25. [New] The semiconductor device of claim 23, further comprising a layer of oxide on the spacer and the oxide active area, the layer of oxide being formed by a polycide reoxidation and forming a smile at the boundary between the feature and the oxide active area.

26. [New] An electronic device comprising:

a first layer of oxide;

a feature over the first layer of oxide, the feature having a surface;

a boundary between the first layer of oxide and the feature; and

a spacer only on the surface of the feature.

27. [New] The electronic device of claim 26 wherein the spacer is deposited on the surface of the feature extending to and terminating at the boundary.

28. [New] The electronic device of claim 26 wherein:

the first layer of oxide comprises a layer of gate oxide;

the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;

the spacer comprises silicon nitride or an amorphous silicon film; and

the surface of the feature comprises sidewalls of the electrode.

29. [New] The electronic device of claim 26, further comprising a second layer of oxide on the spacer and the first layer of oxide, the second layer of oxide forming a smile at the boundary between the feature and the first layer of oxide.

30. [New] An electronic device comprising:

a first layer of oxide;

a feature over the first layer of oxide, the feature having a surface;

a boundary between the first layer of oxide and the feature;

a spacer only on the surface of the feature; and

a second layer of oxide on the spacer and the first layer of oxide, the second layer of oxide forming a smile at the boundary between the feature and the first layer of oxide.

31. [New] The electronic device of claim 30 wherein:

the first layer of oxide comprises a layer of gate oxide;

the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;

the spacer comprises silicon nitride or an amorphous silicon film and the spacer is deposited on the surface of the feature extending to and terminating at the boundary; and

the surface of the feature comprises sidewalls of the electrode.

32. [New] A semiconductor device comprising:

a layer of a first material;

a feature over the layer of the first material, the feature having a surface;

a boundary between the layer of the first material and the feature; and

a spacer only on the surface of the feature.

33. [New] The semiconductor device of claim 32 wherein the layer of the first material comprises a first layer of oxide.

34. [New] The semiconductor device of claim 33 wherein:

the first layer of oxide comprises a layer of gate oxide;

the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;

the spacer comprises silicon nitride or an amorphous silicon film and the spacer is deposited on the surface of the feature extending to and terminating at the boundary; and

the surface of the feature comprises sidewalls of the electrode.

35. [New] The semiconductor device of claim 33, further comprising a second layer of oxide on the spacer and the first layer of oxide, the second layer of oxide forming a smile at the boundary between the feature and the first layer of oxide.

36. [New] An electronic device comprising:

a first layer of oxide;

an electrode on the first layer of oxide, the electrode having sidewalls; and

a spacer deposited only on the sidewalls of the electrode, the spacer extending to and terminating at a boundary between the first layer of oxide and the sidewalls of the electrode.

37. [New] The electronic device of claim 36 wherein:

the first layer of oxide comprises a layer of gate oxide;

the electrode comprises polysilicon, a refractory metal, and a dielectric, or undoped silicon; and

the spacer comprises silicon nitride or an amorphous silicon film.

38. [New] The electronic device of claim 36, further comprising a second layer of oxide on the spacer and the first layer of oxide, the second layer of oxide forming a smile at the boundary between the first layer of oxide and the sidewalls of the electrode.

39. [New] A semiconductor device, comprising:

a first layer of oxide;

a feature protruding from the first layer of oxide and having sidewalls, the feature including:

a polysilicon portion;

a portion of conductive material deposited on the polysilicon portion; and

a spacer selectively deposited only on the sidewalls of the feature; and

a second layer of oxide deposited on the semiconductor device, wherein the spacer is interposed between the second layer of oxide and the sidewalls of the feature.

40. [New] The semiconductor device of claim 39, wherein the spacer comprises silicon nitride or an amorphous silicon film and the portion of conductive material comprises tungsten silicide.

41. [New] A semiconductor device, comprising:

a first layer of oxide;

a feature protruding from the first layer of oxide and having sidewalls, the feature comprising:

a layer of polysilicon;

one or more layers of conductive materials deposited on the layer of polysilicon, wherein at least one of the layers comprises tungsten silicide; and

a silicon nitride spacer selectively deposited only on the sidewalls of the feature; and

a second layer of oxide deposited on the semiconductor device, wherein the silicon nitride spacer is interposed between the second layer of oxide and the sidewalls of the feature.

42. [New] A gate electrode, comprising:

one or more layers of conductive materials etched to form a feature having sidewalls exposing the layers;

a selectively deposited spacer, wherein the spacer is deposited only on the sidewalls of the feature;

a layer of oxide disposed over the gate electrode.

43. [New] The gate electrode of claim 42, wherein the layers comprise tungsten silicide and the selectively deposited spacer comprises silicon nitride or an amorphous silicon film.

REMARKS

In response to the office action dated June 9, 1998, Applicant respectfully requests reconsideration of the application in view of the following remarks. Pending claims 1-22 have been canceled without prejudice and new claims 23-43 have been added to more particularly point out and distinctly claim the subject matter which the Applicant regards as the invention. No new matter has been added.